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## **Erratum: Strain-Engineered Graphene Grown on Hexagonal Boron Nitride by Molecular Beam Epitaxy**

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The following statement has been omitted from the 'Additional Information' section of the HTML version of this Article:

"Data Availability: The images and spectra on which this paper is based may be publicly accessed and are stored at 10.17639/nott.35".

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